

said radicals and removes materials to be cleaned, the improvement comprising introducing said cleaning gas containing said radicals directly into said film-forming chamber.

5. (Amended) A cleaning method for a plasma film-forming chamber according to claim 4, including in said cleaning operation, introducing inert gas into said film-forming chamber in addition to said cleaning gas containing radicals, exciting said inert gas to inert ions, and cleaning said film-forming chamber with the chemical reaction of said radicals and with the sputtering of said inert gas ions.

#### REMARKS

The foregoing amendments to the specification and the claims correct indefinite terminology and grammatical errors. These amendments are considered to place the application in better condition for examination purposes and early allowance.

Respectfully submitted,

CAROTHERS AND CAROTHERS



Floyd B. Carothers  
Attorney for Shin Asari et al.  
445 Fort Pitt Blvd., Suite 500  
Pittsburgh, PA 15219

FBC:jkc  
(412)471-3575  
(412)281-2180 FAX

**APPENDIX: MARKED UP VERSION OF AMENDMENTS**  
**TO THE SPECIFICATION AND CLAIMS**

**ABSTRACT OF THE DISCLOSURE**

[In a] A plasma film-forming apparatus which includes a film-forming chamber in which a substrate is arranged, a film-forming gas introducing pipe is connected to a supply source of a film-forming gas at its first end, a shower plate [through] having numerous holes [of] through which a second end of [said] the film-forming gas introducing pipe [communicate] communicates with [said] the film-forming chamber, film-gas exciting means for exciting film-forming gas introduced through [said] the shower plate into [said] the film-forming[,] chamber to form a film on the surface of [said] the substrate with the chemical reaction, radicals-producing means which excites [said] the cleaning gas and produces radicals, and cleaning-gas introducing means which introduces [said] the cleaning gas containing [said] the radicals into [said] the film-forming chamber[, the improvement in which said]. The apparatus is improved by the cleaning-gas introducing means [communicate] communicating directly with [said] the film-forming chamber.

## SUMMARY OF THE INVENTION

Accordingly, it is an object of this invention to provide a plasma film-forming apparatus and [the] a cleaning method [that] wherein the dissipation of the radicals to be introduced into the film-forming chamber can be prevented.

Another object of this invention is to provide a plasma film-forming apparatus and [the] a cleaning method [that] wherein the radicals [as] of the cleaning gas produced outside the film-forming chamber, can be effectively used for cleaning the film-forming chamber.

In accordance with one aspect of the invention, [in] a plasma film-forming apparatus is provided which includes a film-forming chamber in which a substrate is arranged, a film-forming gas introducing pipe is connected to a supply source of a film-forming gas at its first end, a shower plate [through] having numerous holes [of] through which a second end of said film-forming gas introducing pipe [communicate] communicates with said film-forming chamber, film-gas exciting means for exciting film-forming gas introduced through said shower plate into said film-forming chamber, to form a film on the surface of said substrate with [the] a chemical reaction, radicals-producing means which excites aid cleaning gas and produces radicals, and cleaning-gas introducing means which introduces said cleaning gas containing said radicals into said film-forming chamber, and the improvement resides in [which] said cleaning-gas introducing means [communicate] communicating directly with said film-forming chamber. [film-forming chamber.]

In accordance with another aspect of the invention, [in] a cleaning method [of] for a plasma film-forming apparatus is provided which, in the film-forming operation, introduces a film-forming gas through a shower plate having numerous holes into a film-forming chamber, excites the introduced gas and forms a film, with [the] a chemical reaction, on a surface of

[illegible]



[of] said cleaning-gas[,] into said film-forming chamber and cleans said film-forming chamber by chemical reaction of said radicals and removes materials to be cleaned, the improvement [in which] comprising introducing said cleaning gas containing said radicals [is introduced] directly into said film-forming chamber.

5. (Amended) A cleaning method [of] for a plasma film-forming chamber according to claim 4, [in which,] including in said cleaning operation, introducing inert gas [is introduced] into said film-forming chamber [besides] in addition to said cleaning gas containing radicals, exciting said inert gas [is excited] to [be] inert ions, and cleaning said film-forming chamber [is cleaned] with the chemical reaction of said radicals and with the sputtering of said inert gas ions.

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